



Check for Samples: ADS7886

#### **FEATURES**

- 1-MHz Sample Rate Serial Device
- 12-Bit Resolution
- Zero Latency
- 20-MHz Serial Interface
- Supply Range: 2.35 V to 5.25 V
- Typical Power Dissipation at 1 MSPS:
  - 3.9 mW at 3-V  $V_{DD}$
  - 7.5 mW at 5-V V<sub>DD</sub>
- INL ±1.25 LSB Maximum, ±0.65 LSB (Typical)
- DNL ±1 LSB Maximum, +0.4 / -0.65 LSB (Typical)
- Typical AC Performance:
   72.25 dB SINAD, -84 dB THD
- Unipolar Input Range: 0 V to V<sub>DD</sub>
- Power Down Current: 1 μA
- Wide Input Bandwidth: 15 MHz at 3 dB
- 6-Pin SOT23 and SC70 Packages

#### **APPLICATIONS**

- Base Band Converters in Radio Communication
- Motor Current/Bus Voltage Sensors in Digital Drives
- Optical Networking (DWDM, MEMS Based Switching)
- Optical Sensors
- Battery Powered Systems
- Medical Instrumentations
- High-Speed Data Acquisition Systems
- High-Speed Closed-Loop Systems

#### DESCRIPTION

The ADS7886 is a 12-bit, 1-MSPS analog-to-digital converter (ADC). The device includes a capacitor based SAR A/D converter with inherent sample and hold. The serial interface in each device is controlled by the  $\overline{CS}$  and SCLK signals for glueless connections with microprocessors and DSPs. The input signal is sampled with the falling edge of  $\overline{CS}$ , and SCLK is used for conversion and serial data output.

The device operates from a wide supply range from 2.35 V to 5.25 V. The low power consumption of the device makes it suitable for battery-powered applications. The device also includes a powerdown feature for power saving at lower conversion speeds.

The high level of the digital input to the device is not limited to device  $V_{DD}$ . This means the digital input can go as high as 5.25 V when device supply is 2.35 V. This feature is useful when digital signals are coming from other circuit with different supply levels. Also this relaxes restriction on power up sequencing.

The ADS7886 is available in 6-pin SOT23 and SC70 packages and is specified for operation from -40°C to 125°C.

Table 1. Micro-Power Miniature SAR Converter Family

BIT	< 300 KSPS	300 KSPS - 1.25 MSPS
12-Bit	ADS7866 (1.2 V <sub>DD</sub> to 3.6 V <sub>DD</sub> )	ADS7886 (2.35 V <sub>DD</sub> to 5.25 V <sub>DD</sub> )
10-Bit	ADS7867 (1.2 V <sub>DD</sub> to 3.6 V <sub>DD</sub> )	ADS7887 (2.35 V <sub>DD</sub> to 5.25 V <sub>DD</sub> )
8-Bit	ADS7868 (1.2 V <sub>DD</sub> to 3.6 V <sub>DD</sub> )	ADS7888 (2.35 V <sub>DD</sub> to 5.25 V <sub>DD</sub> )



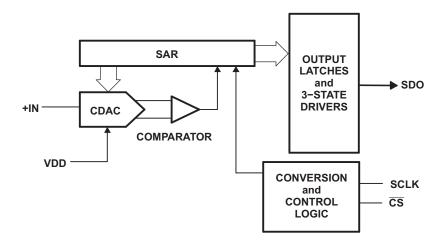
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This integrated circuit can be damaged by ESD. Texas Instruments recommends that all integrated circuits be handled with appropriate precautions. Failure to observe proper handling and installation procedures can cause damage.

ESD damage can range from subtle performance degradation to complete device failure. Precision integrated circuits may be more susceptible to damage because very small parametric changes could cause the device not to meet its published specifications.



### PACKAGE/ORDERING INFORMATION(1)

DEVICE	MAXIMUM INTEGRAL LINEARITY (LSB)	MAXIMUM DIFFER- ENTIAL LINEARITY (LSB)	NO MISSING CODES AT RESOLUTION (BIT)	PACK- AGE TYPE	PACK- AGE DESIG- NATOR	TEMPERATURE RANGE	PACKAGE MARKING	ORDERING INFORMATION	TRANSPORT MEDIA QUANTITY
				6-Pin	DBV		BBAQ	ADS7886SBDBVT	Tape and reel 250
ADS7886SB	±1.25	±1	12	SOT23	DBV	40°C to 125°C	BBAQ	ADS7886SBDBVR	Tape and reel 3000
AD370003B		Ξ1		6-Pin SC70	DCK		BNL	ADS7886SBDCKT	Tape and reel 250
								ADS7886SBDCKR	Tape and reel 3000
				6-Pin	DBV/		BBAQ	ADS7886SDBVT	Tape and reel 250
AD070000	±2	±2		SOT23	DBV		DDAQ	ADS7886SDBVR	Tape and reel 3000
ADS7886S	±2	±2	11	6-Pin	DCK	-40°C to 125°C		ADS7886SDCKT	Tape and reel 250
				SC70	DCK		BNL	ADS7886SDCKR	Tape and reel 3000

<sup>(1)</sup> For most current package and ordering information, see the Package Option Addendum at the end of this document, or see the TI website at www.ti.com.



## ABSOLUTE MAXIMUM RATINGS(1)

		UNIT		
+IN to AGND		-0.3 V to +V <sub>DD</sub> +0.3 V		
+V <sub>DD</sub> to AGND		−0.3 V to 7 V		
Digital input voltage to GND		-0.3 V to (7 V)		
Digital output to GND		-0.3 V to (+V <sub>DD</sub> + 0.3 V)		
Operating temperature range		-40°C to 125°C		
Storage temperature range		−65°C to 150°C		
Junction temperature (T <sub>J</sub> Max)		150°C		
Power dissipation, SOT23 and S	C70 packages	$(T_J Max-T_A)/\theta_{JA}$		
O Thermelimnedense	SOT23	295.2°C/W		
θ <sub>JA</sub> Thermal impedance	SC70	351.3°C/W		
Load tomporature, coldering	Vapor phase (60 sec)	215°C		
Lead temperature, soldering	Infrared (15 sec)	220°C		

<sup>(1)</sup> Stresses above those listed under absolute maximum ratings may cause permanent damage to the device. Exposure to absolute maximum conditions for extended periods may affect device reliability.

## **ELECTRICAL CHARACTERISTICS**

 $+V_{DD} = 2.35 \text{ V to } 5.25 \text{ V}, T_A = -40^{\circ}\text{C to } 125^{\circ}\text{C}, f_{\text{(sample)}} = 1 \text{ MHz (unless otherwise noted)}$ 

	PARAMETER	TEST CONDITIONS	MIN	TYP	MAX	UNIT
ANAL	OG INPUT		1		,	
	Full-scale input voltage span <sup>(1)</sup>		0		$V_{DD}$	V
	Absolute input voltage range	+IN	-0.2		V <sub>DD</sub> +0.2	V
Cı	Input capacitance (2)			21		pF
I <sub>lkg</sub>	Input leakage current	T <sub>A</sub> = 125°C		40		nA
SYSTE	M PERFORMANCE					
	Resolution			12		Bits
	No missing codes	ADS7886SB	12			Bits
	No missing codes	ADS7886S	11			DIIS
INII	Into and popling ority	ADS7886SB	-1.25	±0.65	1.25	LSB <sup>(3)</sup>
INL	Integral nonlinearity	ADS7886S	2		2	LOD
DNL	Differential poplingarity	ADS7886SB	-1	+0.4/-0.65	1	LSB
	Differential nonlinearity	ADS7886S	-2		2	
_	Offset error <sup>(4)</sup>	V <sub>DD</sub> = 2.35 V to 3.6 V	-2.5	-2.5 ±0.5		LSB
Eo	Offset error 17	V <sub>DD</sub> = 4.75 V to 5.25 V	-2	±0.5	2	LSB
E <sub>G</sub>	Gain error		-1.75	±0.5	1.75	LSB
SAMP	LING DYNAMICS					
	Conversion time	20-MHz SCLK	760	800		ns
	Acquisition time		325			ns
	Maximum throughput rate	20-MHz SCLK			1	MHz
	Aperture delay			5		ns
	Step Response			160		ns
	Overvoltage recovery			160		ns
DYNA	MIC CHARACTERISTICS					
CND	Cianal to naine ratio	$V_{DD} = 2.35 \text{ V to } 3.6 \text{ V}, f_{I} = 100 \text{ kHz}$	69	71.25		٩D
SNR	Signal-to-noise ratio	$V_{DD} = 4.75 \text{ V to } 5.25 \text{ V}, f_I = 100 \text{ kHz}$	70	72.25		dB

<sup>(1)</sup> Ideal input span; does not include gain or offset error.(2) See Figure 28 for details on the sampling circuit.

LSB means least significant bit.

Measured relative to an ideal full-scale input.



## **ELECTRICAL CHARACTERISTICS (continued)**

 $+V_{DD}$  = 2.35 V to 5.25 V,  $T_A$  = -40 °C to 125 °C,  $f_{(sample)}$  = 1 MHz (unless otherwise noted)

	PARAMETER	TEST CONDITIONS	MIN	TYP	MAX	UNIT	
OINIAD	O'constitution of the same of the same of	V <sub>DD</sub> = 2.35 V to 3.6 V, f <sub>I</sub> = 100 kHz	69	71.25		JD	
SINAD	Signal-to-noise and distortion	$V_{DD} = 4.75 \text{ V to } 5.25 \text{ V, } f_{I} = 100 \text{ kHz}$	70	72.25		dB	
THD	Total harmonic distortion (5)	f <sub>I</sub> = 100 kHz		-84		dB	
SFDR	Spurious free dynamic range	f <sub>I</sub> = 100 kHz		85.5		dB	
	Full power bandwidth	At –3 dB		15		MHz	
DIGITA	L INPUT/OUTPUT						
Logic fa	mily — CMOS						
.,	I Pale Toward Computer violations	V <sub>DD</sub> = 2.35 V to 3.6 V	1.8		5.25	V	
$V_{IH}$	High-level input voltage	V <sub>DD</sub> = 3.6 V to 5.25 V	2.4		5.25	V	
	Law Israel Construction	V <sub>DD</sub> = 5 V			0.8		
$V_{IL}$	Low-level input voltage	V <sub>DD</sub> = 3 V			0.4	V	
V <sub>OH</sub>	High-level output voltage	I <sub>(source)</sub> = 200 μA	V <sub>DD</sub> -0.2				
V <sub>OL</sub>	Low-level output voltage	$I_{(sink)} = 200 \mu A$			0.4	V	
POWER	SUPPLY REQUIREMENTS						
+V <sub>DD</sub>	Supply voltage		2.35	3.3	5.25	V	
		V <sub>DD</sub> = 2.35 V to 3.6 V, 1-MHz throughput		1.3	1.5		
	Supply current (normal mode)	V <sub>DD</sub> = 4.75 V to 5.25 V, 1-MHz throughput		1.5	2	mA	
		V <sub>DD</sub> = 2.35 V to 3.6 V, static state			1.1		
		V <sub>DD</sub> = 4.75 V to 5.25 V, static state			1.5		
	Device device state events average	SCLK off			1		
	Power down state supply current	SCLK on (20 MHz)			200	μA	
	Device Paringformat A Mile thoughout	V <sub>DD</sub> = 3 V		3.9	4.5	>	
	Power dissipation at 1-MHz throughput	V <sub>DD</sub> = 5 V		7.5	10	mW	
	Dower discinction in static state	V <sub>DD</sub> = 3 V			3.3	2010/	
	Power dissipation in static state	V <sub>DD</sub> = 5 V			7.5	mW	
	Power up time				0.1	μs	
	Invalid conversions after power up or reset				1		

<sup>(5)</sup> Calculated on the first nine harmonics of the input frequency.



## TIMING REQUIREMENTS (see Figure 1 and Figure 2)

All specifications typical at  $T_A = -40$ °C to 125°C,  $V_{DD} = 2.35$  V to 5.25 V (unless otherwise specified).

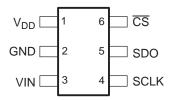
	PARAMETER		TEST CONDITIONS(1)	MIN	TYP	MAX	UNIT			
	Communications times	AD07000	V <sub>DD</sub> = 3 V			16 × t <sub>SCLK</sub>				
t <sub>conv</sub>	Conversion time	ADS7866	V <sub>DD</sub> = 5 V			16 × t <sub>SCLK</sub>	ns			
	Minimum quiet time needed from bu	us 3-state to start	V <sub>DD</sub> = 3 V	40			ns			
t <sub>q</sub>	of next conversion		V <sub>DD</sub> = 5 V	40						
	Delevidade Alexander (a)		V <sub>DD</sub> = 3 V		15	25				
t <sub>d1</sub>	Delay time, $\overline{CS}$ low to first data (0)	out	V <sub>DD</sub> = 5 V		13	25	ns			
	0-1		V <sub>DD</sub> = 3 V	10						
t <sub>su1</sub>	Setup time, CS low to SCLK low		V <sub>DD</sub> = 5 V	10			ns			
	Delevities 200 K (ellies to 000		V <sub>DD</sub> = 3 V		15	25				
t <sub>d2</sub>	Delay time, SCLK falling to SDO		V <sub>DD</sub> = 5 V		13	25	ns			
	Hold time COLK follows to date well	J(2)	V <sub>DD</sub> < 3 V	7						
t <sub>h1</sub>	Hold time, SCLK falling to data valid	3(-)	V <sub>DD</sub> > 5 V	5.5			ns			
	Delay time 16th CCLV falling adds	to CDO 2 ototo	V <sub>DD</sub> = 3 V		10	25	ns			
t <sub>d3</sub>	Delay time, 16th SCLK falling edge	to SDO 3-state	V <sub>DD</sub> = 5 V		8	20	113			
	Dulas duration OC	V <sub>DD</sub> = 3 V	25	40						
t <sub>w1</sub>	Pulse duration, CS		V <sub>DD</sub> = 5 V	25	40		ns			
	Delay time, CS high to SDO 3-state		V <sub>DD</sub> = 3 V		17	30	ns			
t <sub>d4</sub>	belay time, CS high to SDO 3-state		V <sub>DD</sub> = 5 V		15	25				
	Dulas duration CCLK high		V <sub>DD</sub> = 3 V	0.4 × t <sub>SCLK</sub>						
t <sub>wH</sub>	Pulse duration, SCLK high		V <sub>DD</sub> = 5 V	0.4 × t <sub>SCLK</sub>			ns			
	Dulas duration CCLV law		V <sub>DD</sub> = 3 V	0.4 × t <sub>SCLK</sub>			20			
$t_{wL}$	Pulse duration, SCLK low	V <sub>DD</sub> = 5 V					ns			
	Fragues & CLV		V <sub>DD</sub> = 3 V			20	NAL I-			
	Frequency, SCLK		V <sub>DD</sub> = 5 V			20	MHz			
	Delay time, second falling edge of o		V <sub>DD</sub> = 3 V	-2		5				
t <sub>d5</sub>	enter in powerdown (use min spec enter in powerdown) Figure 2	not to accidently	V <sub>DD</sub> = 5 V	-2		5	ns			
	Delay time, CS and 10th falling edg		$V_{DD} = 3 V$	2		-5				
t <sub>d6</sub>	enter in powerdown (use max spec enter in powerdown) Figure 2	not to accidently	V <sub>DD</sub> = 5 V	2		-5	ns			

<sup>3-</sup>V Specifications apply from 2.35 V to 3.6 V, and 5-V specifications apply from 4.75 V to 5.25 V. With 50-pf load.



#### **DEVICE INFORMATION**

#### SOT23/SC70 PACKAGE (TOP VIEW)



#### **TERMINAL FUNCTIONS**

TERI	TERMINAL I/O		DESCRIPTION				
NAME	NO.	1/0	DESCRIPTION				
$V_{DD}$	1	_	Power supply input also acts like a reference voltage to ADC.				
GND	2	_	Ground for power supply, all analog and digital signals are referred with respect to this pin.				
VIN	3	I	Analog signal input				
SCLK	4	I	Serial clock				
SDO	5	0	Serial data out				
CS	6	I	Chip select signal, active low				

### NORMAL OPERATION

The cycle begins with the falling edge of  $\overline{CS}$ . This point is indicated as **a** in Figure 1. With the falling edge of  $\overline{CS}$ , the input signal is sampled and the conversion process is initiated. The device outputs data while the conversion is in progress. The data word contains 4 leading zeros, followed by 12-bit data in MSB first format.

The falling edge of  $\overline{CS}$  clocks out the first zero, and a zero is clocked out on every falling edge of the clock until the third edge. Data is in MSB first format with the MSB being clocked out on the 4th falling edge. On the 16th falling edge of SCLK, SDO goes to the 3-state condition. The conversion ends on the 16th falling edge of SCLK. The device enters the acquisition phase on the first rising edge of SCLK after the 13th falling edge. This point is indicated by **b** in Figure 1.

 $\overline{\text{CS}}$  can be asserted (pulled high) after 16 clocks have elapsed. It is necessary not to start the next conversion by pulling  $\overline{\text{CS}}$  low until the end of the quiet time ( $t_q$ ) after SDO goes to 3-state. To continue normal operation, it is necessary that  $\overline{\text{CS}}$  is not pulled high until point  $\mathbf{b}$ . Without this, the device does not enter the acquisition phase and no valid data is available in the next cycle. (Also refer to power down mode for more details.)  $\overline{\text{CS}}$  going high any time after the conversion start aborts the ongoing conversion and SDO goes to 3-state.

The high level of the digital input to the device is not limited to device  $V_{DD}$ . This means the digital input can go as high as 5.25 V when the device supply is 2.35 V. This feature is useful when digital signals are coming from another circuit with different supply levels. Also, this relaxes the restriction on power up sequencing. However, the digital output levels ( $V_{OH}$  and  $V_{OL}$ ) are governed by  $V_{DD}$  as listed in the *Electrical Characteristics* table.

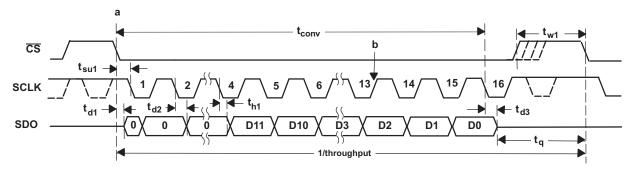


Figure 1. Interface Timing Diagram



### **POWER DOWN MODE**

The device enters power down mode if  $\overline{CS}$  goes high anytime after the 2nd SCLK falling edge to before the 10th SCLK falling edge. Ongoing conversion stops and SDO goes to 3-state under this power down condition as shown in Figure 2.

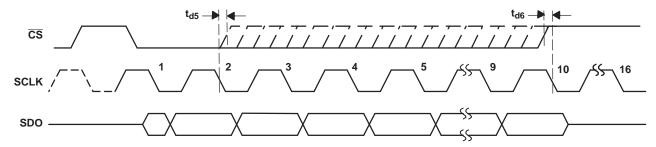


Figure 2. Entering Power Down Mode

A dummy cycle with  $\overline{CS}$  low for more than 10 SCLK falling edges brings the device out of power down mode. For the device to come to the fully powered up condition it takes 1  $\mu s$ .  $\overline{CS}$  can be pulled high any time after the 10th falling edge as shown in Figure 3. It is not necessary to continue until the 16th clock if the next conversion starts 1  $\mu s$  after  $\overline{CS}$  going low of the dummy cycle and the quiet time ( $t_q$ ) condition is met.

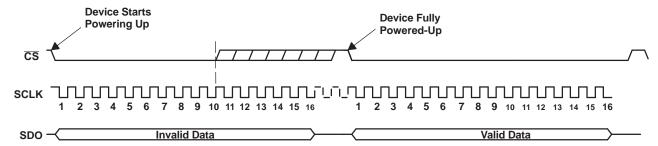


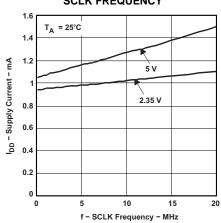
Figure 3. Exiting Power Down Mode



## TYPICAL CHARACTERISTICS

## SUPPLY CURRENT SUPPLY VOLTAGE 1.6 f<sub>s</sub> = 1 MSPS, f<sub>SCLK</sub> = 20 MHz 125°C 1.5 I<sub>DD</sub> - Supply Current - mA 1.4 1.3 1.2 1.1 2.35 3.075 4.525 5.25 V<sub>DD</sub> - Supply Voltage - V

SUPPLY CURRENT vs SCLK FREQUENCY



SUPPLY CURRENT vs

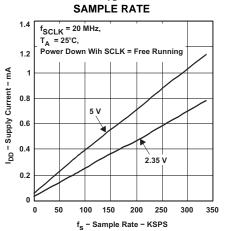
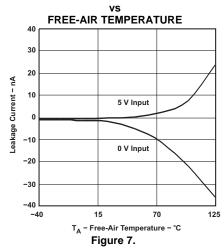


Figure 4. Figure 5.

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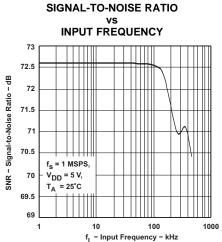
Figure 6.

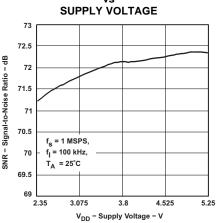
#### ANALOG INPUT LEAKAGE CURRENT











SIGNAL-TO-NOISE RATIO

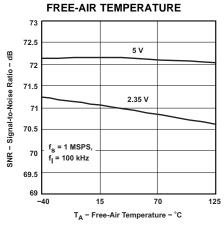
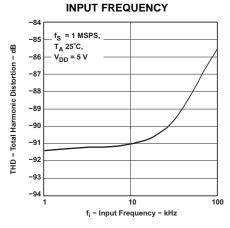


Figure 10.

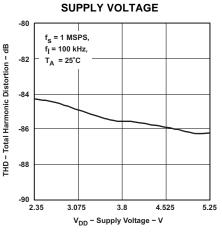
Figure 8.

**TOTAL HARMONIC DISTORTION** 



TOTAL HARMONIC DISTORTION

Figure 9.



TOTAL HARMONIC DISTORTION

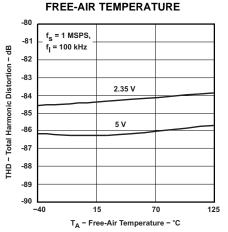


Figure 12.

Figure 11.

SPURIOUS FREE DYNAMIC RANGE

87

86

85.5

85

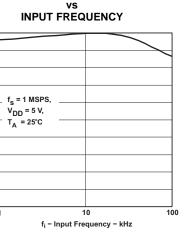
84

83.5

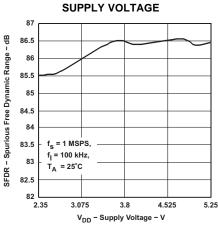
83

82 5 82

SFDR – Spurious Free Dynamic Range – dB



SPURIOUS FREE DYNAMIC RANGE



SPURIOUS FREE DYNAMIC RANGE SUPPLY VOLTAGE

Figure 13.

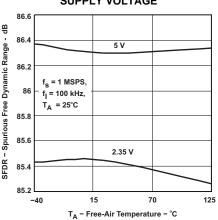


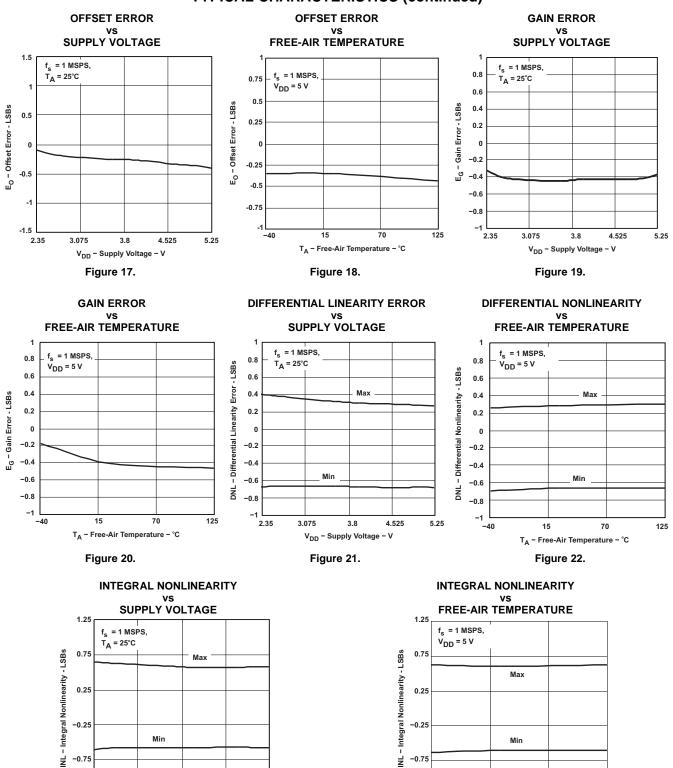
Figure 15.

Figure 14.

Figure 16.



## **TYPICAL CHARACTERISTICS (continued)**



3.075

3.8

V<sub>DD</sub> – Supply Voltage – V

Figure 23.

4.525

5.25

2.35

70

125

-1.25

-40

15

Figure 24.

T<sub>A</sub> - Free-Air Temperature - °C



## **TYPICAL CHARACTERISTICS (continued)**

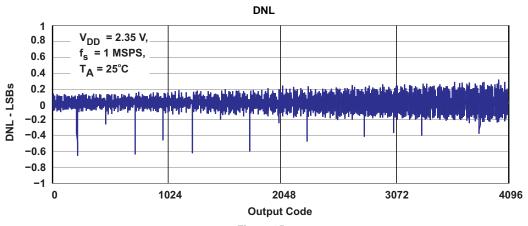


Figure 25.

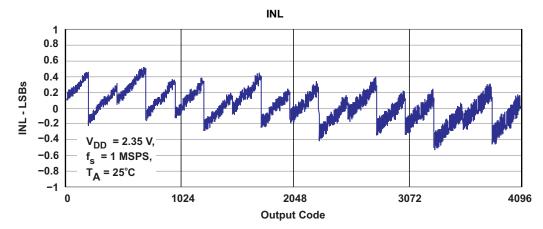


Figure 26.

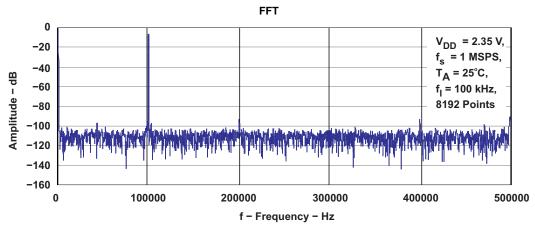


Figure 27.



#### APPLICATION INFORMATION

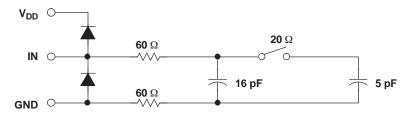


Figure 28. Typical Equivalent Sampling Circuit

### Driving the VIN and V<sub>DD</sub> Pins

The VIN input should be driven with a low impedance source. In most cases additional buffers are not required. In cases where the source impedance exceeds 200  $\Omega$ , using a buffer would help achieve the rated performance of the converter. The THS4031 is a good choice for the driver amplifier buffer.

The reference voltage for the A/D converter is derived from the supply voltage internally. The devices offer limited low-pass filtering functionality on-chip. The supply to these converters should be driven with a low impedance source and should be decoupled to the ground. A 1-µF storage capacitor and a 10-nF decoupling capacitor should be placed close to the device. Wide, low impedance traces should be used to connect the capacitor to the pins of the device. The ADS7886 draws very little current from the supply lines. The supply line can be driven by either:

- · Directly from the system supply.
- A reference output from a low drift and low drop out reference voltage generator like REF3030 or REF3130.
   The ADS7886 operates from a wide range of supply voltages. The actual choice of the reference voltage generator would depend upon the system. Figure 30 shows one possible application circuit.
- A low-pass filtered system supply followed by a buffer, like the zero-drift OPA735, can also be used in cases
  where the system power supply is noisy. Care should be taken to ensure that the voltage at the V<sub>DD</sub> input
  does not exceed 7 V to avoid damage to the converter. This can be done easily using single supply CMOS
  amplifiers like the OPA735. Figure 31 shows one possible application circuit.

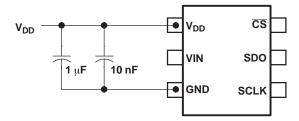


Figure 29. Supply/Reference Decoupling Capacitors

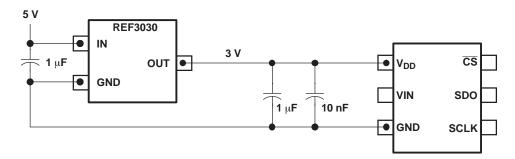


Figure 30. Using the REF3030 Reference



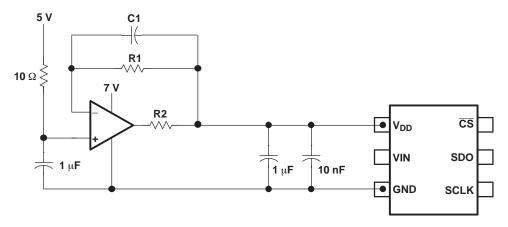


Figure 31. Buffering with the OPA735

## SLAS492A - SEPTEMBER 2005-REVISED NOVEMBER 2009



## **REVISION HISTORY**

Cł	hanges from Original (SEPTEMBER 2005) to Revision A  Added V <sub>IH</sub> information		
•	Added V <sub>IH</sub> information	4	
•	Changed V <sub>IH</sub> information	4	





11-Apr-2013

#### **PACKAGING INFORMATION**

Orderable Device	Status (1)	Package Type	Package Drawing	Pins	Package Qty	Eco Plan	Lead/Ball Finish	MSL Peak Temp	Op Temp (°C)	Top-Side Markings	Samples
ADS7886SBDBVR	ACTIVE	SOT-23	DBV	6	3000	Pb-Free (RoHS Exempt)	CU SN	Level-2-260C-1 YEAR	-40 to 125	BBAQ	Samples
ADS7886SBDBVT	ACTIVE	SOT-23	DBV	6	250	Pb-Free (RoHS Exempt)	CU SN	Level-2-260C-1 YEAR	-40 to 125	BBAQ	Samples
ADS7886SBDCKR	ACTIVE	SC70	DCK	6	3000	Pb-Free (RoHS Exempt)	CU SN	Level-2-260C-1 YEAR	-40 to 125	BNL	Samples
ADS7886SBDCKT	ACTIVE	SC70	DCK	6	250	Pb-Free (RoHS Exempt)	CU SN	Level-2-260C-1 YEAR	-40 to 125	BNL	Samples
ADS7886SDBVR	ACTIVE	SOT-23	DBV	6	3000	Pb-Free (RoHS Exempt)	CU SN	Level-2-260C-1 YEAR	-40 to 125	BBAQ	Samples
ADS7886SDBVT	ACTIVE	SOT-23	DBV	6	250	Pb-Free (RoHS Exempt)	CU SN	Level-2-260C-1 YEAR	-40 to 125	BBAQ	Samples
ADS7886SDCKR	ACTIVE	SC70	DCK	6	3000	Pb-Free (RoHS Exempt)	CU SN	Level-2-260C-1 YEAR	-40 to 125	BNL	Samples
ADS7886SDCKT	ACTIVE	SC70	DCK	6	250	Pb-Free (RoHS Exempt)	CU SN	Level-2-260C-1 YEAR	-40 to 125	BNL	Samples

<sup>(1)</sup> The marketing status values are defined as follows:

ACTIVE: Product device recommended for new designs.

LIFEBUY: TI has announced that the device will be discontinued, and a lifetime-buy period is in effect.

NRND: Not recommended for new designs. Device is in production to support existing customers, but TI does not recommend using this part in a new design.

PREVIEW: Device has been announced but is not in production. Samples may or may not be available.

**OBSOLETE:** TI has discontinued the production of the device.

TBD: The Pb-Free/Green conversion plan has not been defined.

**Pb-Free** (RoHS): TI's terms "Lead-Free" or "Pb-Free" mean semiconductor products that are compatible with the current RoHS requirements for all 6 substances, including the requirement that lead not exceed 0.1% by weight in homogeneous materials. Where designed to be soldered at high temperatures, TI Pb-Free products are suitable for use in specified lead-free processes. **Pb-Free** (RoHS Exempt): This component has a RoHS exemption for either 1) lead-based flip-chip solder bumps used between the die and package, or 2) lead-based die adhesive used between the die and leadframe. The component is otherwise considered Pb-Free (RoHS compatible) as defined above.

Green (RoHS & no Sb/Br): TI defines "Green" to mean Pb-Free (RoHS compatible), and free of Bromine (Br) and Antimony (Sb) based flame retardants (Br or Sb do not exceed 0.1% by weight in homogeneous material)

<sup>(2)</sup> Eco Plan - The planned eco-friendly classification: Pb-Free (RoHS), Pb-Free (RoHS Exempt), or Green (RoHS & no Sb/Br) - please check http://www.ti.com/productcontent for the latest availability information and additional product content details.

<sup>(3)</sup> MSL, Peak Temp. -- The Moisture Sensitivity Level rating according to the JEDEC industry standard classifications, and peak solder temperature.



## PACKAGE OPTION ADDENDUM

11-Apr-2013

(4) Multiple Top-Side Markings will be inside parentheses. Only one Top-Side Marking contained in parentheses and separated by a "~" will appear on a device. If a line is indented then it is a continuation of the previous line and the two combined represent the entire Top-Side Marking for that device.

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## PACKAGE MATERIALS INFORMATION

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## TAPE AND REEL INFORMATION





	Dimension designed to accommodate the component width
	Dimension designed to accommodate the component length
K0	Dimension designed to accommodate the component thickness
W	Overall width of the carrier tape
P1	Pitch between successive cavity centers

QUADRANT ASSIGNMENTS FOR PIN 1 ORIENTATION IN TAPE



#### \*All dimensions are nominal

Device	Package Type	Package Drawing		SPQ	Reel Diameter (mm)	Reel Width W1 (mm)	A0 (mm)	B0 (mm)	K0 (mm)	P1 (mm)	W (mm)	Pin1 Quadrant
ADS7886SBDBVR	SOT-23	DBV	6	3000	177.8	9.7	3.2	3.1	1.39	4.0	8.0	Q3
ADS7886SBDBVT	SOT-23	DBV	6	250	177.8	9.7	3.2	3.1	1.39	4.0	8.0	Q3
ADS7886SBDCKR	SC70	DCK	6	3000	177.8	9.7	2.3	2.52	1.2	4.0	8.0	Q3
ADS7886SBDCKT	SC70	DCK	6	250	177.8	9.7	2.3	2.52	1.2	4.0	8.0	Q3
ADS7886SDBVR	SOT-23	DBV	6	3000	177.8	9.7	3.2	3.1	1.39	4.0	8.0	Q3
ADS7886SDBVT	SOT-23	DBV	6	250	177.8	9.7	3.2	3.1	1.39	4.0	8.0	Q3
ADS7886SDCKR	SC70	DCK	6	3000	177.8	9.7	2.3	2.52	1.2	4.0	8.0	Q3
ADS7886SDCKT	SC70	DCK	6	250	177.8	9.7	2.3	2.52	1.2	4.0	8.0	Q3

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\*All dimensions are nominal

Device	Package Type	Package Drawing	Pins	SPQ	Length (mm)	Width (mm)	Height (mm)	
ADS7886SBDBVR	SOT-23	DBV	6	3000	210.0	185.0	35.0	
ADS7886SBDBVT	SOT-23	DBV	6	250	184.0	184.0	50.0	
ADS7886SBDCKR	SC70	DCK	6	3000	184.0	184.0	50.0	
ADS7886SBDCKT	SC70	DCK	6	250	184.0	184.0	50.0	
ADS7886SDBVR	SOT-23	DBV	6	3000	184.0	184.0	50.0	
ADS7886SDBVT	SOT-23	DBV	6	250	184.0	184.0	50.0	
ADS7886SDCKR	SC70	DCK	6	3000	184.0	184.0	50.0	
ADS7886SDCKT	SC70	DCK	6	250	184.0	184.0	50.0	

# DBV (R-PDSO-G6)

## PLASTIC SMALL-OUTLINE PACKAGE



NOTES:

- A. All linear dimensions are in millimeters.
- B. This drawing is subject to change without notice.
- C. Body dimensions do not include mold flash or protrusion. Mold flash and protrusion shall not exceed 0.15 per side.
- D. Leads 1,2,3 may be wider than leads 4,5,6 for package orientation.
- Falls within JEDEC MO-178 Variation AB, except minimum lead width.



# DBV (R-PDSO-G6)

# PLASTIC SMALL OUTLINE



NOTES:

- A. All linear dimensions are in millimeters.
- B. This drawing is subject to change without notice.
- C. Customers should place a note on the circuit board fabrication drawing not to alter the center solder mask defined pad.
- D. Publication IPC-7351 is recommended for alternate designs.
- E. Laser cutting apertures with trapezoidal walls and also rounding corners will offer better paste release. Customers should contact their board assembly site for stencil design recommendations. Example stencil design based on a 50% volumetric metal load solder paste. Refer to IPC-7525 for other stencil recommendations.



# DCK (R-PDSO-G6)

# PLASTIC SMALL-OUTLINE PACKAGE



NOTES: A. All linear dimensions are in millimeters.

- B. This drawing is subject to change without notice.
- C. Body dimensions do not include mold flash or protrusion. Mold flash and protrusion shall not exceed 0.15 per side.
- D. Falls within JEDEC MO-203 variation AB.



# DCK (R-PDSO-G6)

# PLASTIC SMALL OUTLINE



NOTES:

- A. All linear dimensions are in millimeters.
- B. This drawing is subject to change without notice.
- C. Customers should place a note on the circuit board fabrication drawing not to alter the center solder mask defined pad.
- D. Publication IPC-7351 is recommended for alternate designs.
- E. Laser cutting apertures with trapezoidal walls and also rounding corners will offer better paste release. Customers should contact their board assembly site for stencil design recommendations. Example stencil design based on a 50% volumetric metal load solder paste. Refer to IPC-7525 for other stencil recommendations.



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